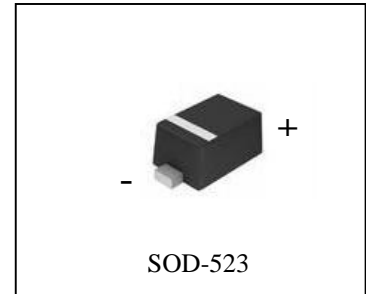


HIGH SPEED SWITCHING DIODE
RB751S-40
FEATURES

Small surface mounting type
 Low reverse current and low forward voltage
 High reliability

MARKING: 5



Maximum Ratings and Electrical Characteristics, Single Diode @TA=25°C

Parameter	Symbol	Limits	Unit
Peak reverse voltage	V_{RM}	40	V
DC reverse voltage	V_R	30	V
Mean rectifying current	I_F	30	mA
Peak forward surge current	I_{FSM}	200	mA
Junction temperature	T_J	125	°C
Storage temperature	T_{stg}	-40-125	°C

ELECTRICAL CHARACTERISTICS (Tamb=25°C unless otherwise specified)

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Forward voltage	V_F			0.37	V	$I_F=1mA$
Reverse current	I_R			0.5	μA	$V_R=30V$
Capacitance between terminals	C_T		2		p	$V_R=1V, f=1MHZ$

RB751S-40 Typical Characteristics

●Electrical characteristic curves (Ta = 25°C)

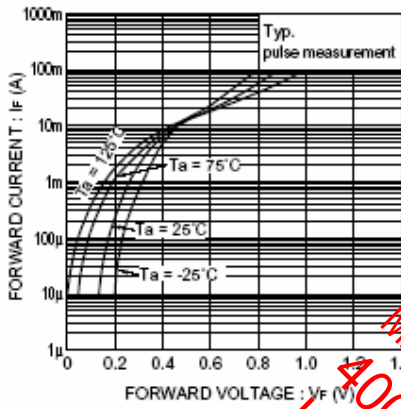


Fig. 1 Forward characteristics

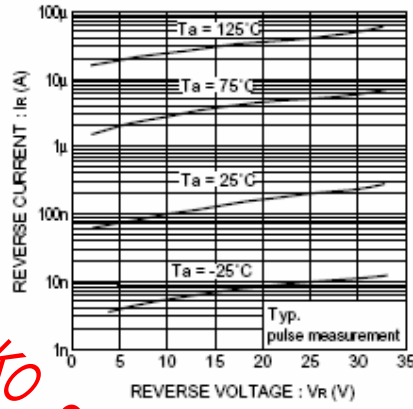


Fig. 2 Reverse characteristics

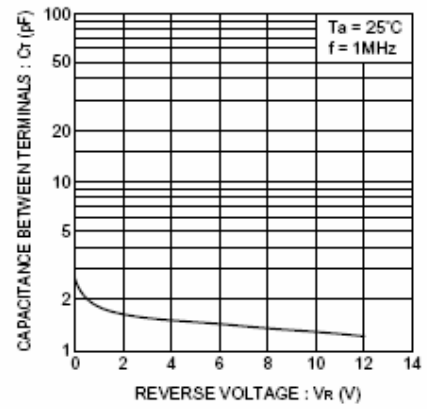


Fig. 3 Capacitance between terminals characteristics

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